7-13GHz Low Noise Amplifier

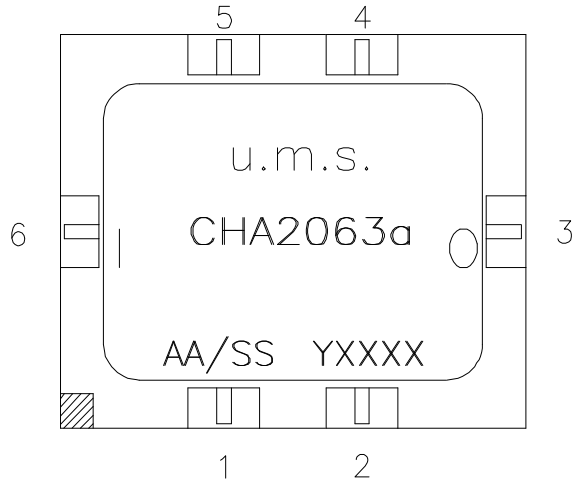
GaAs Monolithic Microwave IC

Description

The CHA2063a is a two-stage wide band monolithic low noise amplifier.

The circuit is manufactured with a PM-HEMT process : 0.25µm gate length, via holes through the substrate, air bridges and electron beam gate lithography.

It is supplied in chip form or in an hermetic leadless ceramic package.



Main Features

Broad band performance 7-13GHz
2.0dB noise figure, 8-13GHz
19dB gain
Low DC power consumption, 40mA
18dBm 3rd order intercept point
Chip size : 1,52 x 1,27 x 0.1mm

Pin Out

1 - NC
2 - NC
3 - RF output
4 - NC
5 - Vdd
6 - RF input

Main Characteristics

Tamb = +25°C, package form

Symbol	Parameter	Min	Typ	Max	Unit
NF	Noise figure, 7-8GHz Noise figure, 8-13GHz		2.5 2.0	3.0 2.5	dB
G	Gain	16	19		dB
ΔG	Gain flatness		± 2.0		dB

ESD Protections : Electrostatic discharge sensitive device observe handling precautions !

United Monolithic Semiconductors S.A.S.
Route Départementale 128 - B.P.46 - 91401 Orsay Cedex France
Tel. : +33 (0)1 69 33 03 08 - Fax : +33 (0)1 69 33 03 09